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UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,713,346 B2  
DATED : March 30, 2004  
INVENTOR(S) : Graham Wolstenholme

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [57], **ABSTRACT,**

Line 2, replace "forming flash memory. In one implementation, a line of" with  
-- forming FLASH memory. In one implementation, a line of --

Column 30,

Line 31, replace "FIG. 1 is a diagrammatic top plan of a semiconductor" with  
-- FIG. 1 is a diagrammatic top plan view of a semiconductor --

Column 6,

Line 10, replace "having portions thereof angled at least 150 from a direction" with  
-- having portions thereof angled at least 15° from a direction --

Column 8,

Line 15, replace "spacer is formed on one of the=source side or the drain side" with  
-- spacer is formed on one of the source side or the drain side --

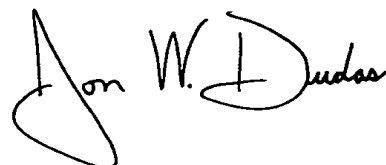
Line 57, replace "A method at forming a line of FLASH memory cells" with -- A  
method of forming a line of FLASH memory cells --

Column 10,

Line 31, replace "insulative sidewall spacer having en innermost surface" with  
-- insulative sidewall spacer having an innermost surface --

Signed and Sealed this

Seventh Day of December, 2004



JON W. DUDAS  
*Director of the United States Patent and Trademark Office*